BUK7Y28-75B

N-channel TrenchMOS standard level FET

Rev. 03 — 18 February 2010 **Objective data sheet**

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using NXP High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- DC-to-DC converters
- Engine management
- General purpose power switching
- Solenoid drivers
- Transmission control

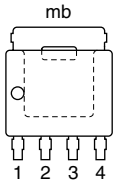
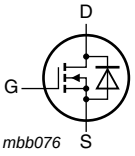
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	-	75	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see Figure 1 and 3	-	-	35.5	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2	-	-	85	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	I_D = 15 A; V_{DS} = 60 V; V_{GS} = 10 V; see Figure 15	-	7.4	-	nC
Static characteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see Figure 12 and 13	-	23	28	mΩ
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 35.5 A; $V_{sup} \leq 75$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	75	mJ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

SOT669 (LFPAK)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7Y28-75B	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	75	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ		-	75	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1 and 3		-	35.5	A
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1		-	25.1	A
I_{DM}	peak drain current	T_{mb} = 25 °C; $t_p \leq 10$ µs; pulsed; see Figure 3		-	142	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2		-	85	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C		-	35.5	A
I_{SM}	peak source current	$t_p \leq 10$ µs; pulsed; T_{mb} = 25 °C		-	142	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 35.5 A; $V_{sup} \leq 75$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	75	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	see Figure 4	[1][2][3]	-	-	J

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[2] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[3] Refer to application note AN10273 for further information.

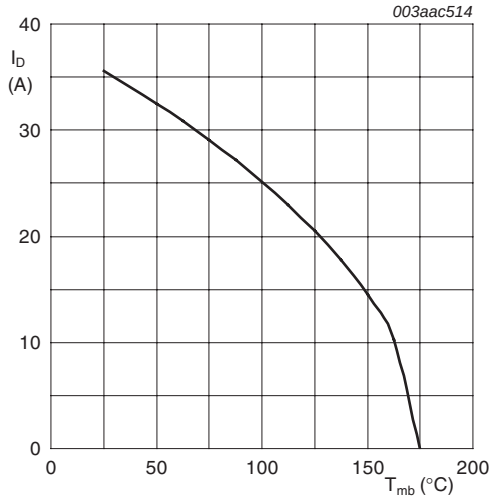
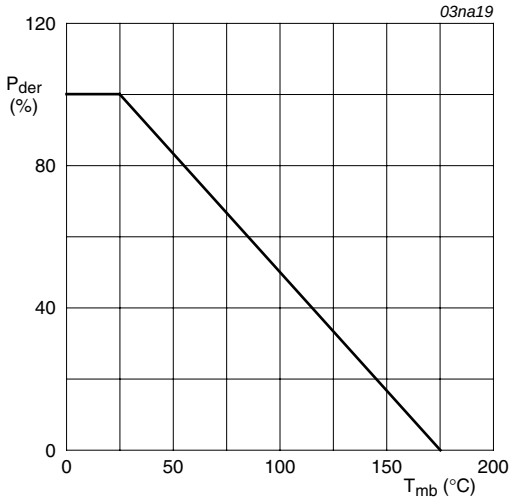
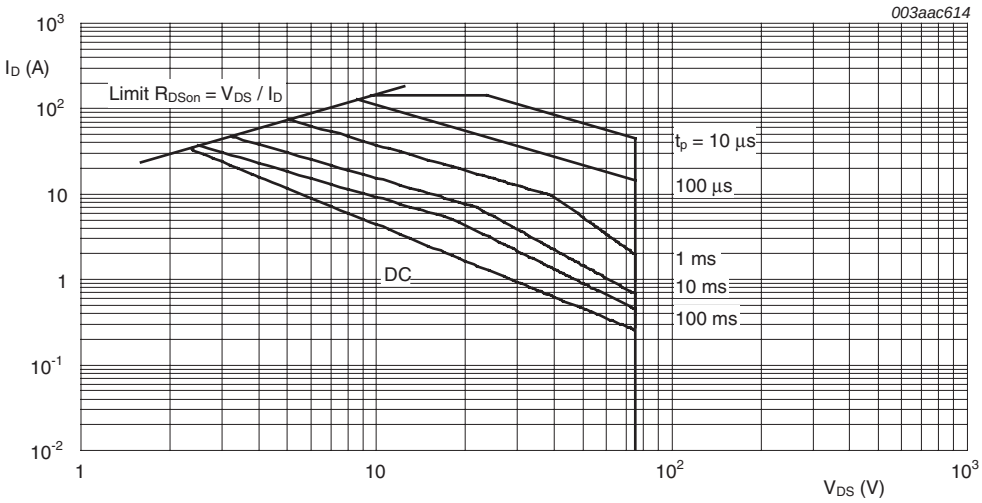


Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25\,°C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

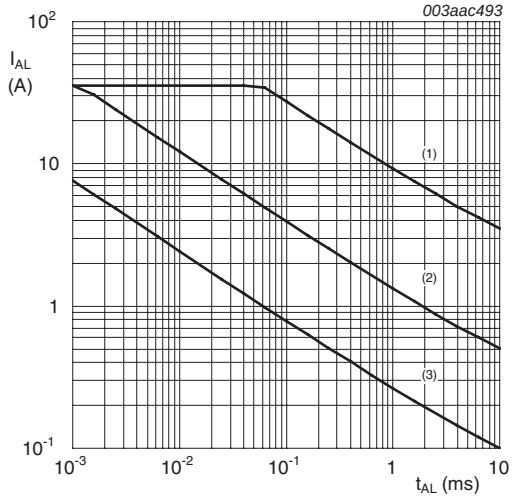


Fig 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	1.76	K/W

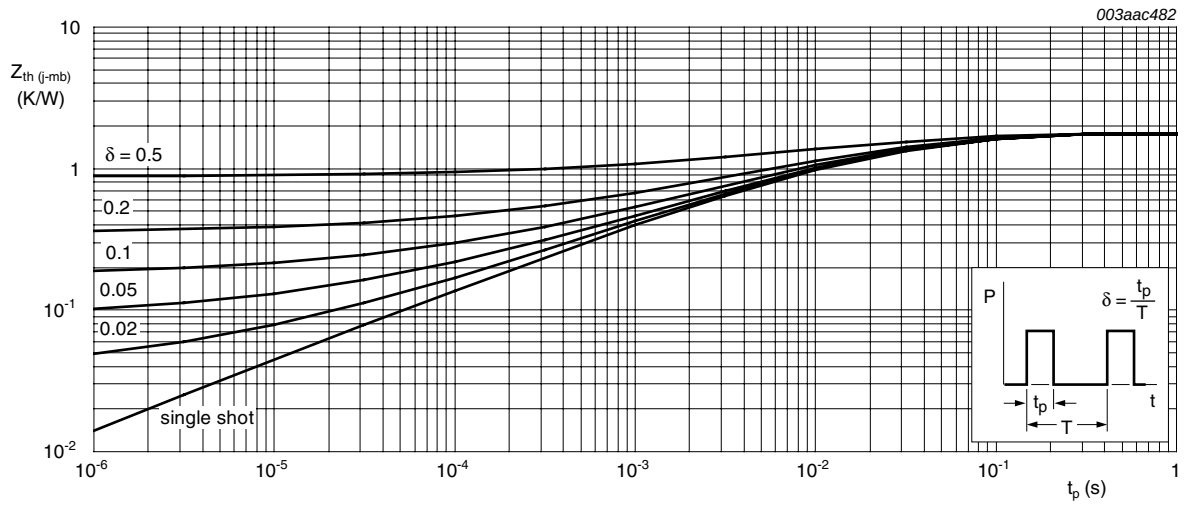
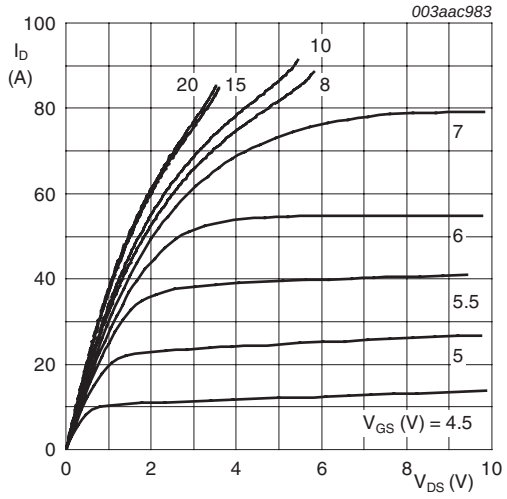


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

6. Characteristics

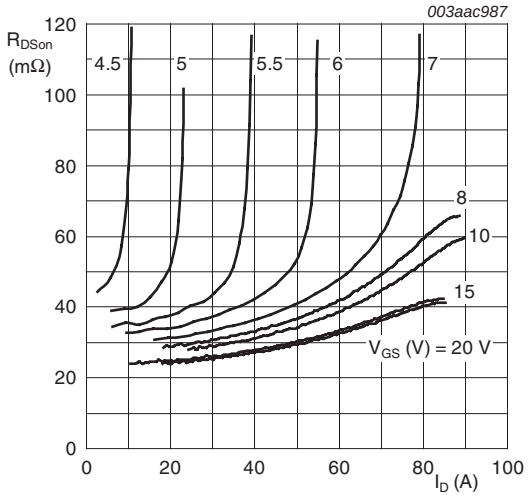
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	75	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	68	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 10 and 11	2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 10	-	-	4.4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 10	1	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 75 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	µA
		V_{DS} = 75 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
I_{GSS}	gate leakage current	V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 °C	-	2	100	nA
		V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 °C	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 15 A; T_j = 175 °C; see Figure 12	-	-	67.2	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see Figure 12 and 13	-	23	28	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 15 A; V_{DS} = 60 V; V_{GS} = 10 V; see Figure 15	-	21.2	-	nC
Q_{GS}	gate-source charge		-	5	-	nC
Q_{GD}	gate-drain charge		-	7.4	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; see Figure 16	-	1063	1417	pF
C_{oss}	output capacitance		-	186	223	pF
C_{rss}	reverse transfer capacitance		-	74	101	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω	-	7	-	ns
t_r	rise time		-	12.6	-	ns
$t_{d(off)}$	turn-off delay time		-	29.8	-	ns
t_f	fall time		-	7.1	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 15 A; V_{GS} = 25 V; T_j = 25 °C; see Figure 14	-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 30 V	-	50	-	ns
Q_r	recovered charge		-	115	-	nC



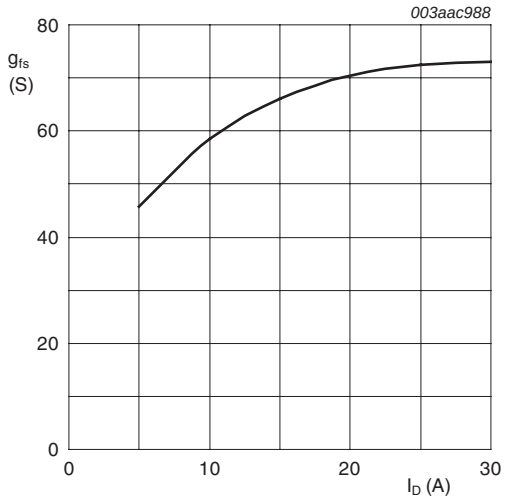
$T_j = 25\,°C$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values.



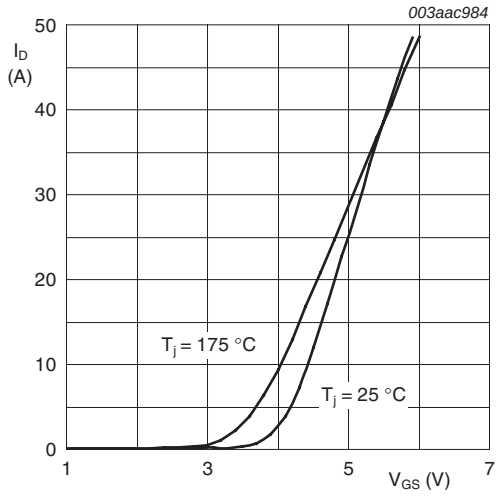
$T_j = 25\,°C$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



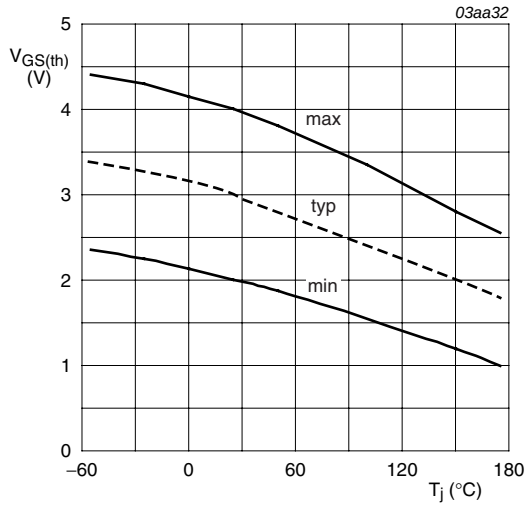
$T_j = 25\,°C; V_{DS} = 25\,V$

Fig 8. Forward transconductance as a function of drain current; typical values.



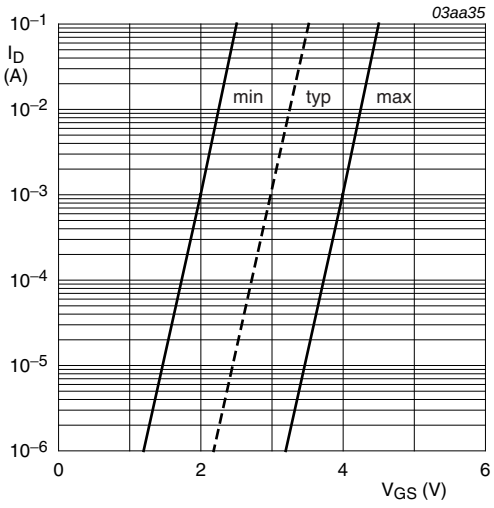
$V_{DS} = 25\,V$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



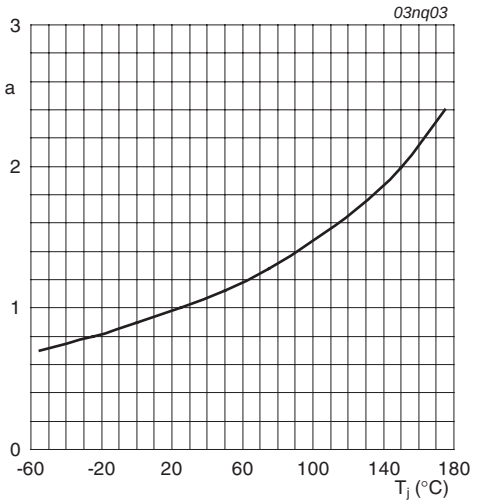
$$I_D = 1\,mA; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



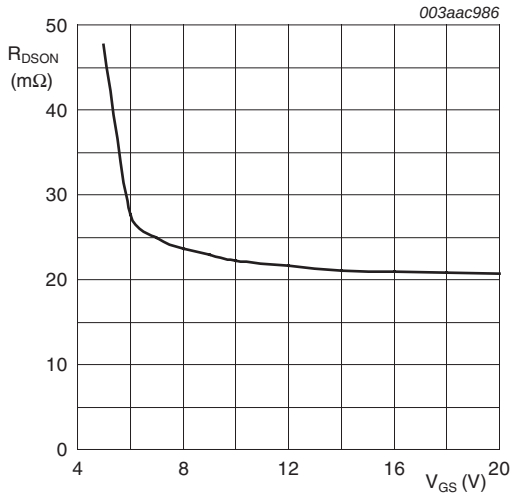
$$T_j = 25\,°C; V_{DS} = 5V$$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



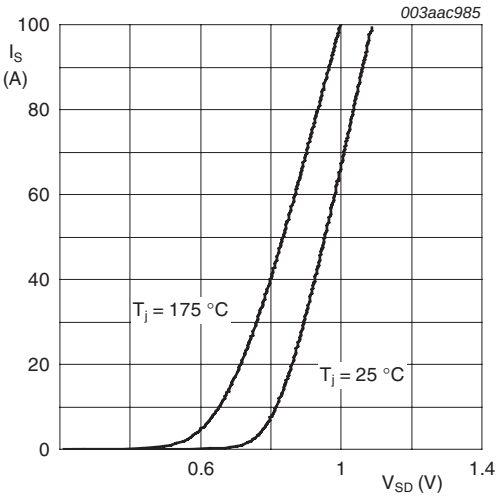
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



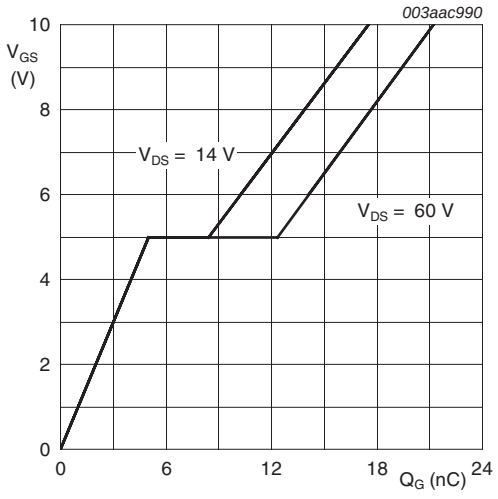
$$T_j = 25\,°C; I_D = 15A$$

Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values.



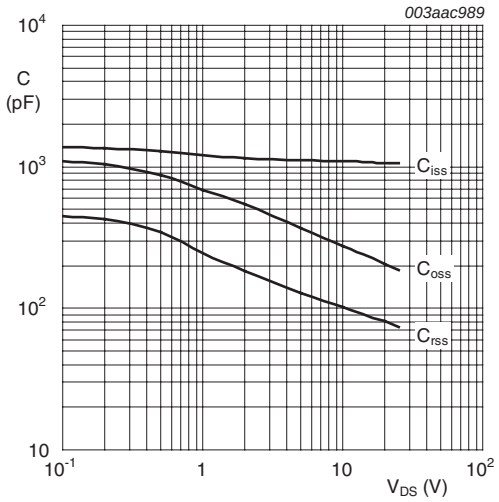
$V_{GS} = 0V$

Fig 14. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$T_j = 25°C; I_D = 15A$

Fig 15. Gate-source voltage as a function of gate charge; typical values.

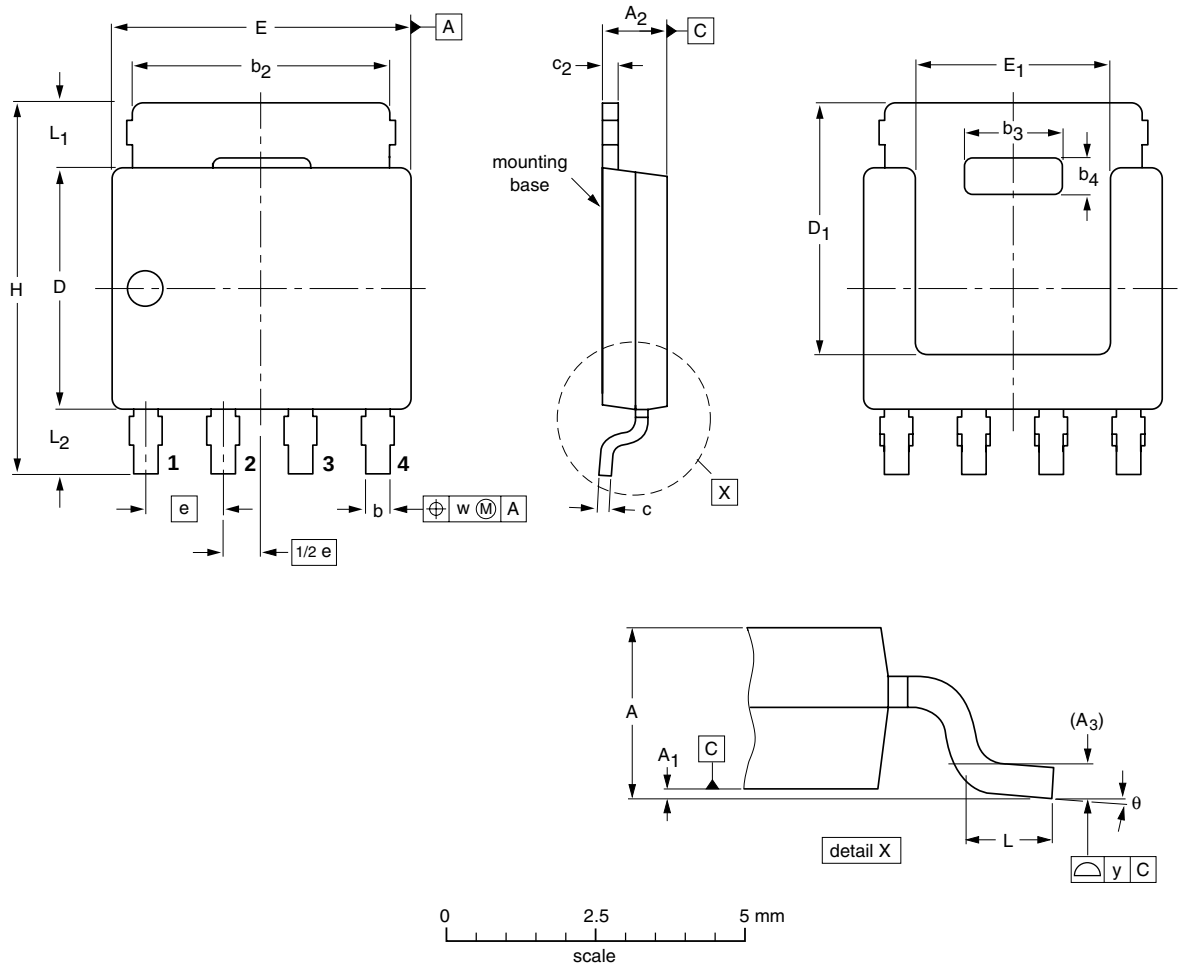


$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.

7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads **SOT669**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	A_2	A_3	b	b_2	b_3	b_4	c	c_2	$D^{(1)}$	$D_1^{(1)}$ max	$E^{(1)}$	$E_1^{(1)}$	e	H	L	L_1	L_2	w	y	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT669		MO-235				~~04-10-13~~ 06-03-16

Fig 17. Package outline SOT669 (LFPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7Y28-75B_3	20100218	Objective data sheet	-	BUK7Y28-75B_2
Modifications:	• Various changes to content.			
BUK7Y28-75B_2	20090803	Objective data sheet	-	BUK7Y28-75B_1
BUK7Y28-75B_1	20081216	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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10. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

11. Contents

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For sales office addresses, please send an email to: salesaddresses@nxp.com

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